

# Dual Common Drain P-Channel PowerTrench<sup>®</sup> MOSFET -20 V, -7 A, 36 m $\Omega$

#### Features

- Max  $r_{S1S2(on)}$  = 36 m $\Omega$  at  $V_{GS}$  = -4.5 V,  $I_D$  = -5.7 A
- Max  $r_{S1S2(on)}$  = 50 m $\Omega$  at V<sub>GS</sub> = -2.5 V, I<sub>D</sub> = -4.6 A
- Low Profile 0.8 mm maximum in the new package MicroFET 2x3 mm
- HBM ESD protection level 2.8 kV (Note 3)
- RoHS Compliant

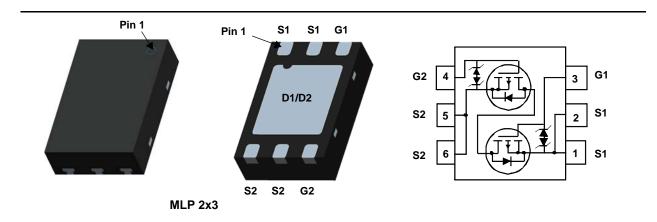


## **General Description**

This device is designed specifically as a single package solution for Li-Ion battery pack protection circuit and other ultra-portable applications. It features two common drain P-channel MOSFETs, which enables bidirectional current flow, on Fairchild's advanced PowerTrench<sup>®</sup> process with state of the art MircoFET Leadframe, the FDMB2308PZ minimizes both PCB space and  $r_{S1S2(on)}$ .

### Application

Li-Ion Battery Pack



#### MOSFET Maximum Ratings T<sub>A</sub> = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V <sub>S1S2</sub>	Source1 to Source2 Voltage			-20	V
V <sub>GS</sub>	Gate to Source Voltage			±12	V
	Source1 to Source2 Current -Continuous	T <sub>A</sub> = 25 °C	(Note 1a)	-7	^
IS1S2	-Pulsed			-30	Α
P <sub>D</sub>	Power Dissipation	T <sub>A</sub> = 25 °C	(Note 1a)	2.2	W
	Power Dissipation	T <sub>A</sub> = 25 °C	(Note 1b)	0.8	vv
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature I	Range		-55 to +150	°C

#### **Thermal Characteristics**

$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	57	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	161	0/11

#### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
308	FDMB2308PZ	MLP 2x3	7"	8 mm	3000 units

FDMB2308PZ Dual Common Drain P-Channel PowerTrench® MOSFET
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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Off Chara	acteristics						
I <sub>S1S2</sub>	Zero Gate Voltage Source1 to Source2 Current	$V_{S1S2} = -16 V, V_{GS} = 0 V$			-1	μΑ	
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 12 \text{ V}, V_{S1S2} = 0 \text{ V}$			±10	μA	
On Chara	octeristics						
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{S1S2}, I_{S1S2} = -250 \ \mu A$	-0.6	-0.9	-1.5	V	
r <sub>S1S2(on)</sub>		$V_{GS} = -4.5 \text{ V}, \ I_{S1S2} = -5.7 \text{ A}$		27	36	1	
	Statia Source1 to Source2 On Resistance	V <sub>GS</sub> = -2.5 V, I <sub>S1S2</sub> = -4.6 A		36	50		
	Static Source1 to Source2 On Resistance	$V_{GS} = -4.5 \text{ V}, \ I_{S1S2} = -5.7 \text{ A},$ $T_J = 125 \ ^{\circ}\text{C}$		35	49	- mΩ	
9fs	Forward Transconductance	V <sub>S1S2</sub> = -5 V, I <sub>S1S2</sub> = -5.7 A		29		S	
Dynamic	Characteristics						
C <sub>iss</sub>	Input Capacitance			2280	3030	pF	
C <sub>oss</sub>	Output Capacitance	V <sub>S1S2</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		361	540	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			339	510	pF	
Switching	g Characteristics						
t <sub>d(on)</sub>	Turn-On Delay Time			14	25	ns	
t <sub>r</sub>	Rise Time	$V_{S1S2}$ = -10 V, $I_{S1S2}$ = -5.7 A V <sub>GS</sub> = -4.5 V, R <sub>GEN</sub> = 6 Ω		33	52	ns	
t <sub>d(off)</sub>	Turn-Off Delay Time			74	118	ns	
t <sub>f</sub>	Fall Time			58	93	ns	
Q <sub>g</sub>	Total Gate Charge	V <sub>S1S2</sub> = -10 V, I <sub>S1S2</sub> = -5.7 A,		22	30	nC	
Q <sub>gs</sub>	Gate1 to Source1 Charge	$V_{G1S1} = -4.5 V, V_{G2S2} = 0 V$		3.6		nC	
Q <sub>gd</sub>	Gate1 to Source2 "Miller" Charge			7.7		nC	
Source1-	Source2 Diode Characteristics						
I <sub>fss</sub>	Maximum Continuous Source1-Source2 Diode Forward Current				-5.7	А	
V <sub>fss</sub>	Source1 to Source2 Diode Forward Voltage	$V_{G1S 1} = 0 V, V_{G2S2} = -4.5 V,$ $I_{fss} = -5.7 A$ (Note 2)		-1	-1.6	V	



a. 57 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper

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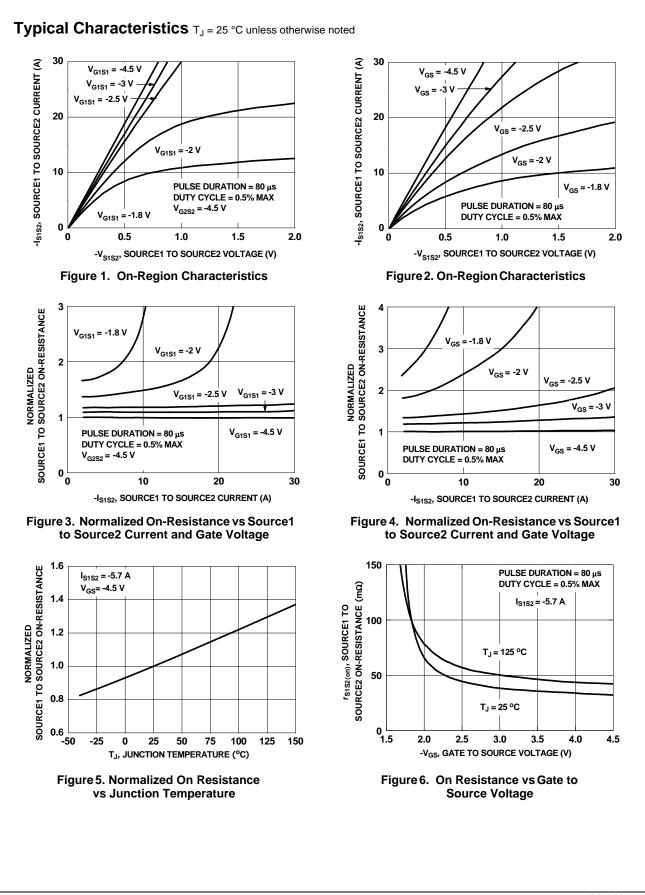
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b. 161 °C/W when mounted on

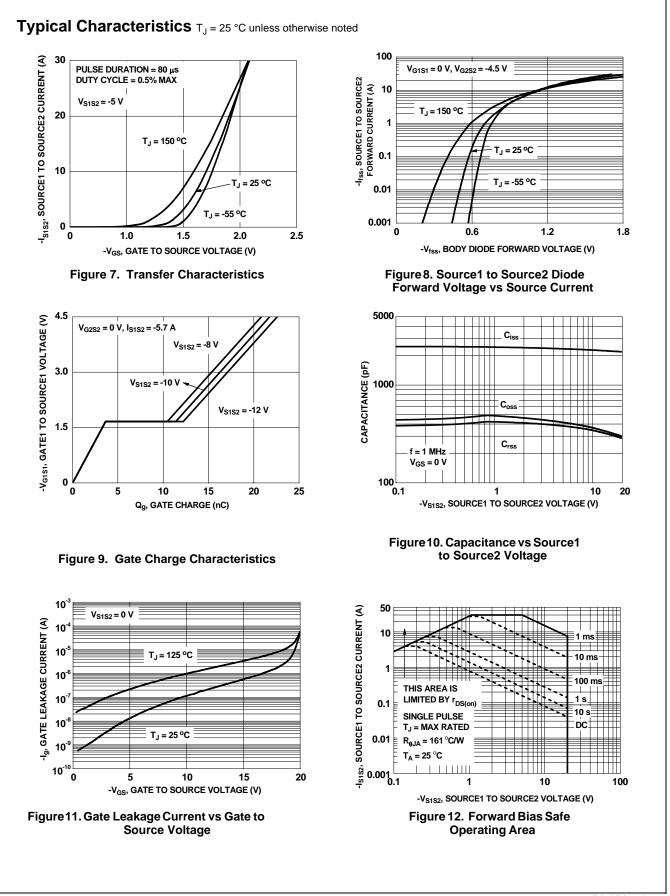
a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300  $\mu s,$  Duty cycle < 2.0%.

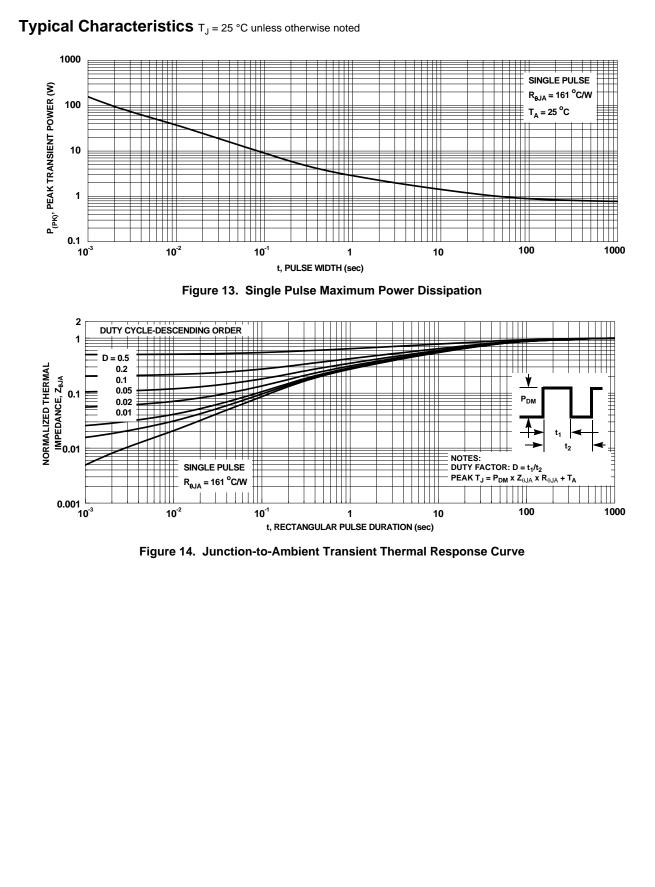
3. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.



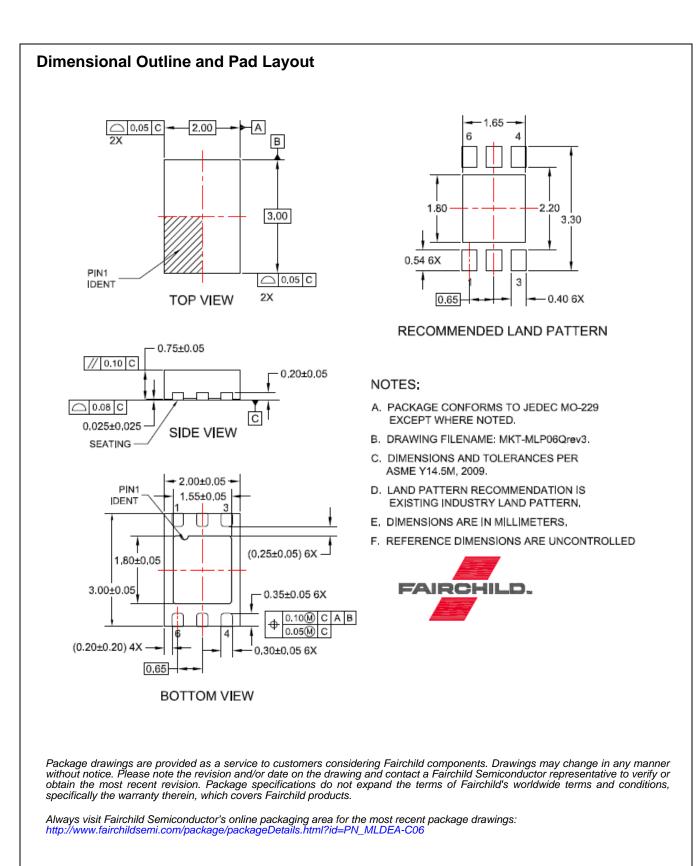
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FDMB2308PZ Rev.C3



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